

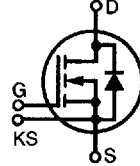


MegaMOS™FRED

IXTN36N50

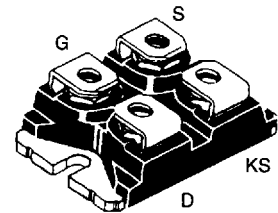
$$\begin{aligned} V_{DSS} &= 500 \text{ V} \\ I_{D25} &= 36 \text{ A} \\ R_{DS(on)} &= 0.12 \Omega \end{aligned}$$

N-Channel Enhancement Mode



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 10 \text{ k}\Omega$	500	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	36	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	133	A
P_D	$T_C = 25^\circ\text{C}$	400	W
T_J		-40 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-40 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz	t = 1 min	2500 V~
	$I_{ISOL} \leq 1 \text{ mA}$	t = 1 s	3000 V~
M_d	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque (M4)	1.5/13	Nm/lb.in.
Weight		30	g

miniBLOC, SOT-227 B



G = Gate, D = Drain,
S = Source, KS = Kelvin Source

Features

- International standard package miniBLOC (ISOTOP compatible)
- Isolation voltage 3000 V~
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low drain-to-case capacitance (< 50 pF)
- Low package inductance (< 10 nH)
- easy to drive and to protect

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 20 \text{ mA}$	2		V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$			$\pm 500 \text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		400 μA
	$V_{GS} = 0 \text{ V}$			2 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			0.12 Ω

Applications

- AC motor speed control
- DC servo and robot drives
- Uninterruptible power systems (UPS)
- Switch-mode and resonant-mode power supplies
- DC choppers

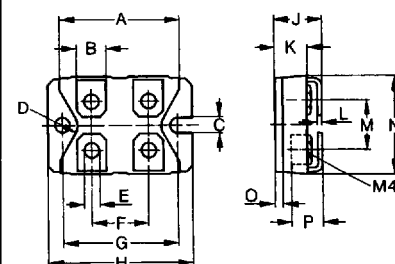
Advantages

- Easy to mount with 2 screws
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulsed	30	38	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		8.5	nF
C_{oss}			0.9	nF
C_{rss}			0.3	nF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 1\ \Omega$, (External)			100 ns
t_r				110 ns
$t_{d(off)}$				220 ns
t_f				105 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		270	350 nC
Q_{gs}			60	90 nC
Q_{gd}			125	200 nC
R_{thJC}			0.31	K/W
R_{thCK}		0.05		K/W

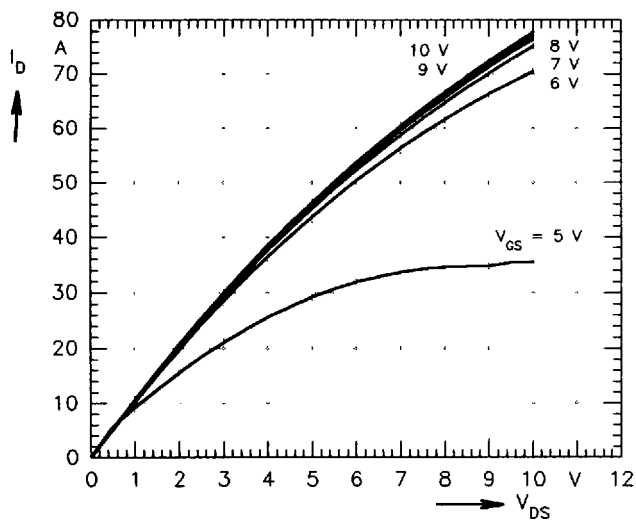
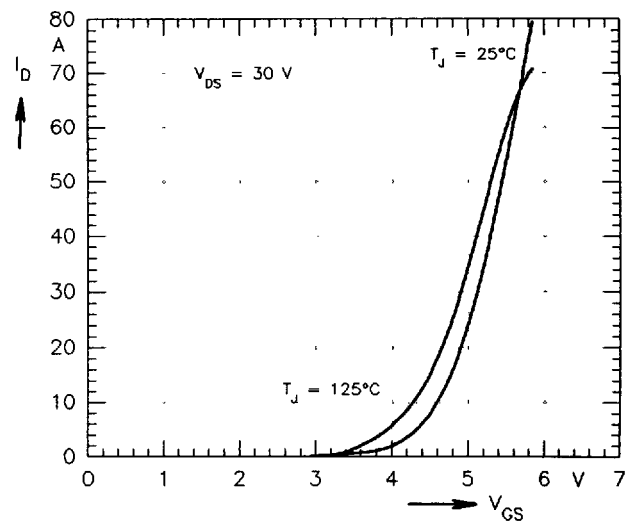
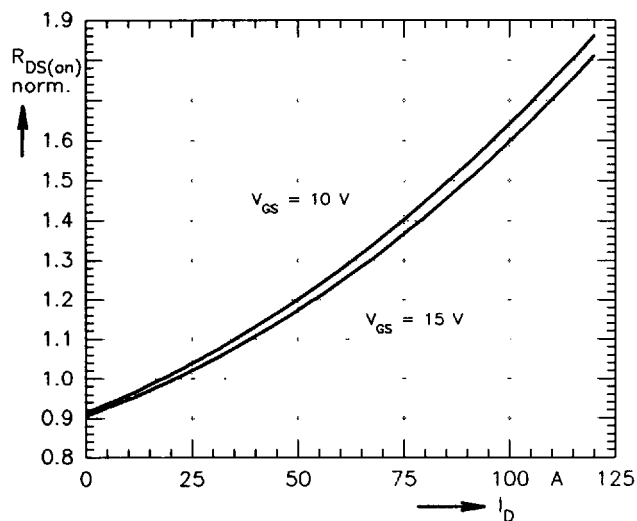
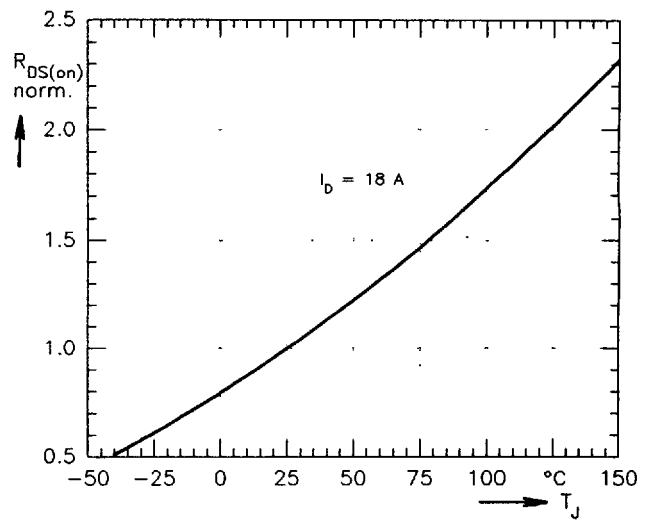
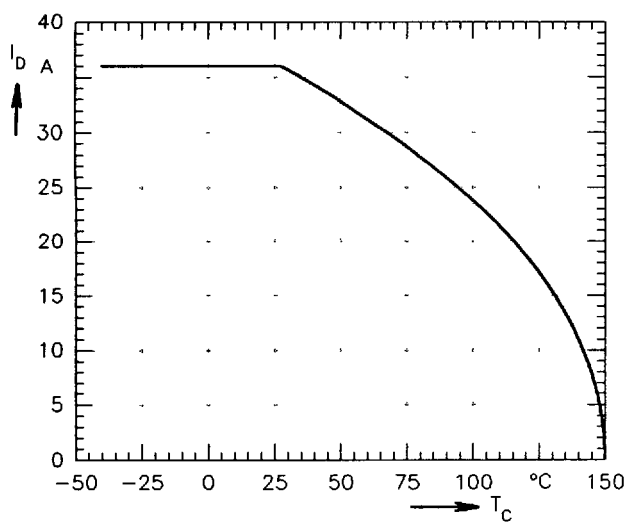
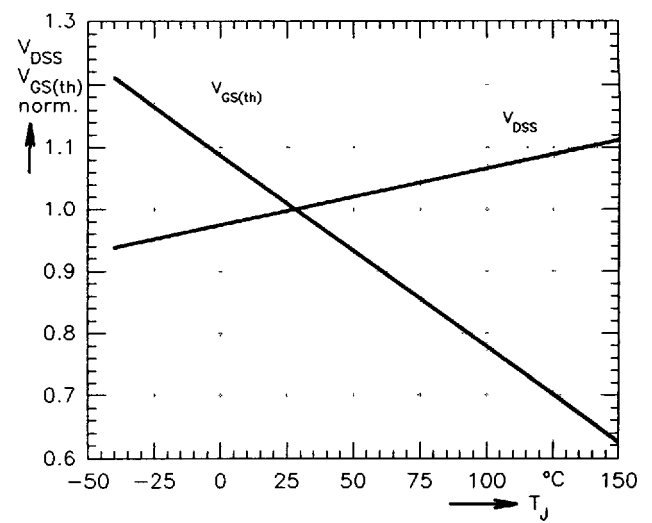
Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0$			36 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			144 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$	600		ns

miniBLOC, SOT 227-B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.5	31.7	1.241	1.249
B	7.8	8.2	0.307	0.323
C	4.0	-	0.158	-
D	4.1	4.3	0.162	0.169
E	4.1	4.3	0.162	0.169
F	14.9	15.1	0.587	0.595
G	30.1	30.3	1.186	1.193
H	38.0	38.2	1.497	1.505
J	11.8	12.2	0.465	0.481
K	8.9	9.1	0.351	0.359
L	0.75	0.85	0.030	0.033
M	12.6	12.8	0.496	0.504
N	25.2	25.4	0.993	1.001
O	1.95	2.05	0.077	0.081
P	-	5.0	-	0.197

Fig. 1 Typ output characteristics, $I_D = f(V_{DS})$ Fig. 2 Typ. transfer characteristics, $I_D = f(V_{GS})$ Fig. 3 Typ. normalized $R_{DS(on)} = f(I_D)$ Fig. 4 Typ. normalized $R_{DS(on)} = f(T_J)$ Fig. 5 Continuous drain current $I_D = f(T_C)$ Fig. 6 Typ. normalized $V_{DS} = f(T_J)$, $V_{GS(th)} = f(T_J)$

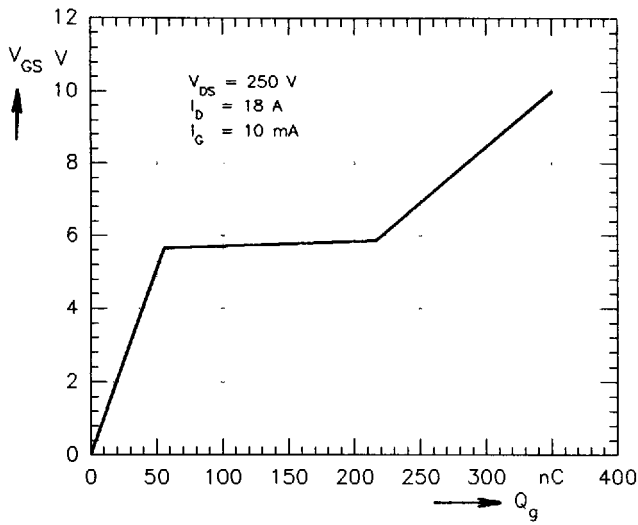


Fig. 7 Typ. turn-on gate charge characteristics, $V_{GS} = f(Q_g)$

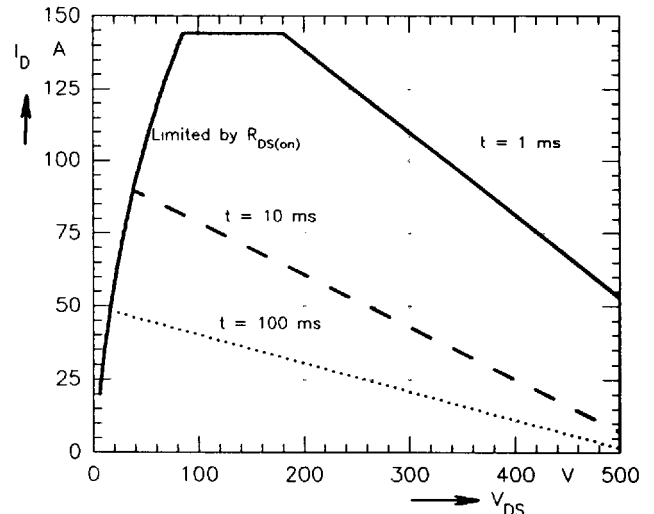


Fig. 8 Forward Bias Safe Operating Area $I_D = f(V_{DS})$

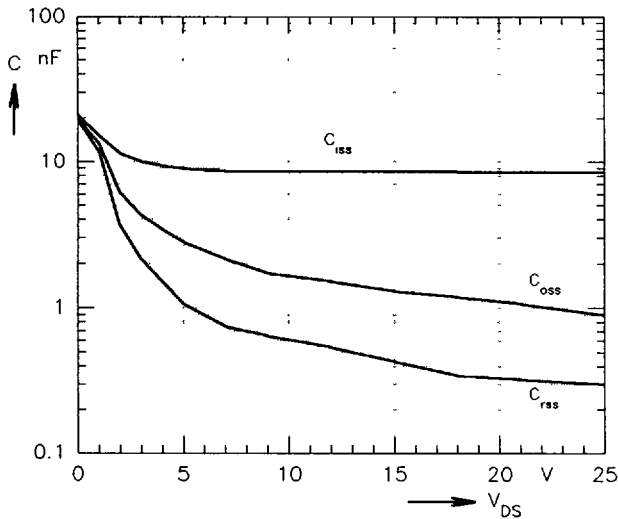


Fig. 9 Typ. capacitances $C = f(V_{DS})$, $f = 1 \text{ MHz}$

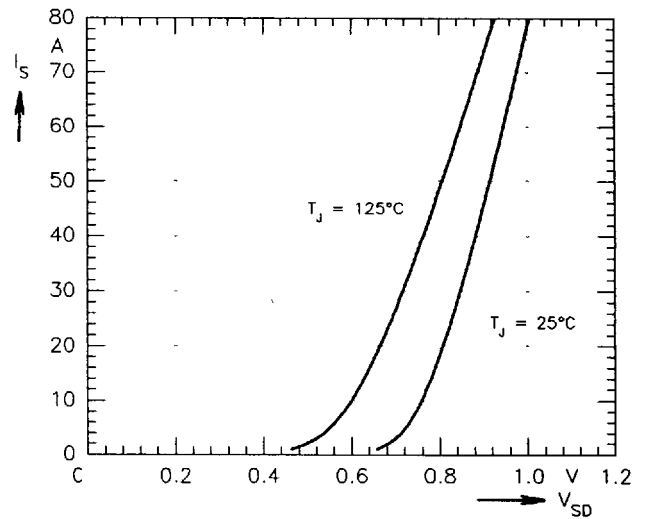


Fig. 10 Typ. forward characteristics of reverse diode $I_S = f(V_{SD})$

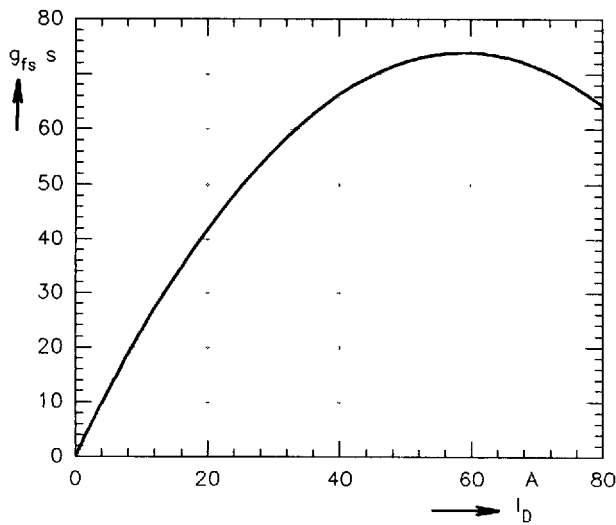


Fig. 11 Typ. transconductance, $g_{fs} = f(I_D)$

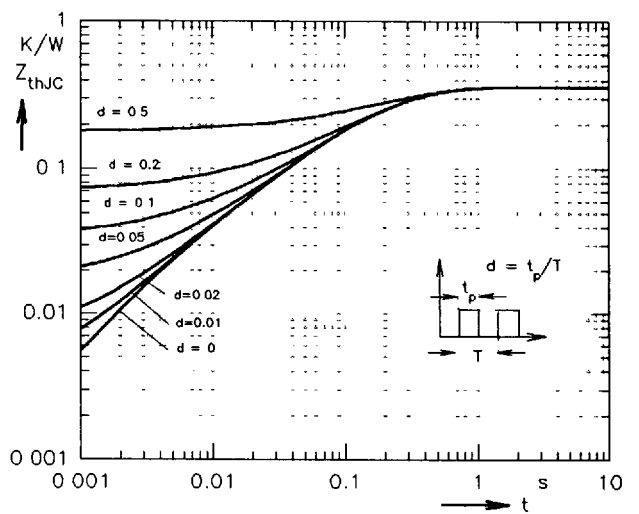


Fig. 12 Transient thermal resistance, $Z_{thJC} = f(t)$